

AMENDMENT TO THE SPECIFICATION

Please amend the specification without prejudice, without admission, without surrender of subject matter, and without any intention of creating any estoppel as to equivalents, as follows.

Please delete the paragraph on page 5, line 13 through page 6, line 2 and insert the following new paragraph:

-----Meanwhile, it has been known that polymethyl silsesquioxane, one of low dielectric silicate matrices of spin-on types, exhibits improved properties for interlayer dielectrics such as low dielectric constant ($k=2.7$) and stability to moisture and heat. However, when exposed to vigorous semiconductor processes such as chemical mechanical planarization (CMP), its film is liable to disruption due to its low mechanical strength. Further, as the pores introduced into the polymethyl silsesquioxane matrix are increased with a view to reducing dielectric constant, it is likely that more drawbacks would occur. For this reason, the present inventors have developed a novel polyalkyl silsesquioxane copolymer having improved mechanical properties and compatibility with porogen by copolymerization of alkyltrialkoxysilane, a monomer for polymerization of polymethyl silsesquioxane, with a, co-bistrialkoxysilyl compound as a comonomer (Korean Patent Unexamined Publication No. 2002-38540).-----